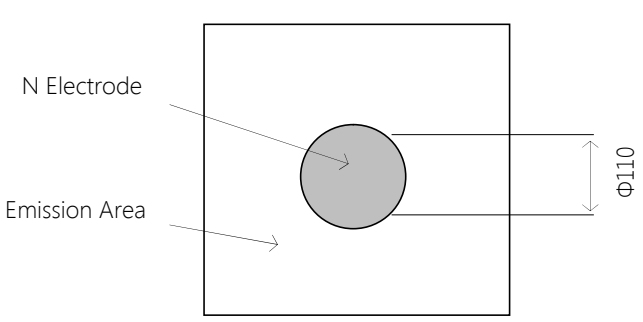
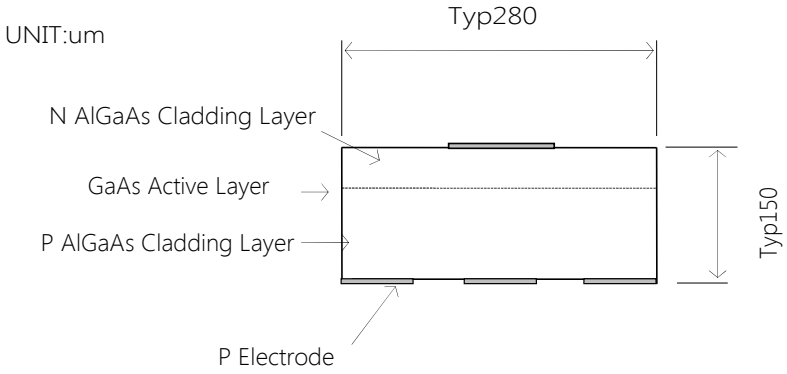
Marktech Optoelectronics

LED Chip Infrared

Product No: **OPC8700-28**

Radiation	Type	Electrodes
Infrared	AlGaAs	N (cathode) up





Physical Characteristics & Structure

Material: AlGaAs

Junction Size: 280um x 280um

Thickness: 150um

Bond Pad Size: 110um diameter

Anode Metalization: Gold Alloy

Cathode Metalization: Gold Alloy

Electrical & Optical Characteristics (Ta = 25ºC)

ITEMS	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	Vf	If=20mA	--	--	1.7	V
Reverse Voltage	Vr	Ir=10uA	5	--	--	V
Radiant Power*	Φe	If=20mA	4.0	--	--	mW
Peak Wavelength	λp	If=20mA	850	870	900	nm
Spectral Bandwidth at 50%	Δλ0.5	If=20mA	--	45	--	nm
Rise Time	Tr	Ifp=100mA Tw=125ns, Duty=25%	--	20	--	ns
Fall Time	Tf	Ifp=100mA Tw=125ns, Duty=25%	--	20	--	ns
Peak Forward Voltage	Vfm	Ifp=400mA Tw=100us, Duty=10%	--	3.1	--	V

* LED chip is mounted on TO-18 gold header without resin coated.

Absolute Maximum Ratings (Ta = 25ºC)

Continuous Maximum Forward Current: 70mA (DC)

Reverse Voltage: 5V (IR=10uA)

Storage Temperature

while on mylar membrane: 0 to 40 ºC

after removal from mylar membrane: -30 to 100 ºC

RoHS COMPLIANT

Pb-Free

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.

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